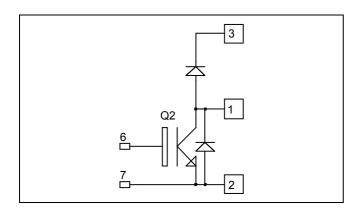


## Boost chopper Trench + Field Stop IGBT4 Power Module

$$V_{CES} = 1200V$$
  
 $I_{C} = 475A @ Tc = 80°C$ 



#### **Application**

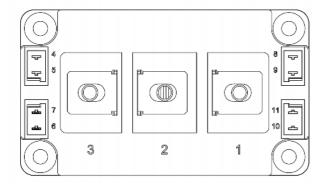
- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

#### **Features**

- Trench + Field Stop IGBT 4 Technology
  - Low voltage drop
  - Low leakage current
  - Low switching losses
  - Soft recovery parallel diodes
  - Low diode VF
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- High level of integration
- M6 power connectors



- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive  $T_C$  of  $V_{CEsat}$
- **RoHS Compliant**



#### Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage		1200	V
$I_{C}$	Continuous Collector Current	$T_C = 25$ °C	610	
	Continuous Conector Current	$T_C = 80$ °C	475	Α
$I_{CM}$	Pulsed Collector Current	$T_C = 25^{\circ}C$	900	
$V_{GE}$	Gate – Emitter Voltage		±20	V
$P_{\mathrm{D}}$	Maximum Power Dissipation	$T_C = 25^{\circ}C$	2080	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125$ °C	800A @ 1100V	

😘 🚓 UTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



### All ratings @ $T_j = 25$ °C unless otherwise specified

#### **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				5	mA
V <sub>CE(sat)</sub>	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.8	2.2	V
		$I_C = 400A$ $T_j = 125^{\circ}$	$T_j = 125$ °C		2.2		ľ
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$ , $I_C = 15mA$		5.0	5.8	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

**Dynamic Characteristics** 

•	Characteristic	Test Conditions	Test Conditions		Typ	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$			24.6		
Coes	Output Capacitance				1.62		nF
$C_{res}$	Reverse Transfer Capacitance	f = 1MHz			1.38		
$Q_{G}$	Gate charge	$V_{GE}$ = -8V / 15V ; $V_{CE}$ =600V $I_{C}$ =400A			2.3		μС
$T_{d(on)}$	Turn-on Delay Time		Inductive Switching (25°C)		200		
$T_{r}$	Rise Time	$V_{GE} = \pm 15V$			40		
$T_{d(off)}$	Turn-off Delay Time	$V_{CE} = 600V$ $I_{C} = 400A$			400		ns
$T_{\rm f}$	Fall Time	$R_G = 1\Omega$		70			
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{CE} = 600V$ $I_{C} = 400A$ $R_{G} = 1\Omega$			220		ns
T <sub>r</sub>	Rise Time				50		
$T_{d(off)}$	Turn-off Delay Time				500		
$T_{\mathrm{f}}$	Fall Time				80		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{CE} = 600V$	$T_J = 150$ °C		33		mJ
$E_{\text{off}}$	Turn-off Switching Energy	$I_{\rm C} = 400 A$ $R_{\rm G} = 1 \Omega$	$T_{\rm J} = 150^{\circ}{\rm C}$		42		mJ
$I_{sc}$	Short Circuit data	$V_{GE} \le 15V$ ; $V_{Bus} = 900V$ $t_p \le 10 \mu s$ ; $T_j = 150 ^{\circ}C$			1600		A

Diode ratings and characteristics

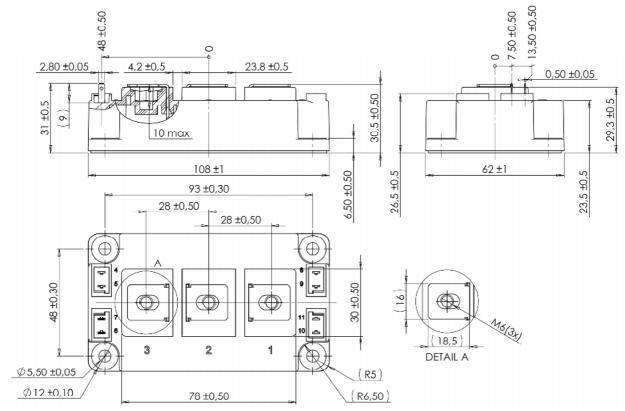
Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$V_{RRM}$	Maximum Repetitive Reverse Voltage			1200			V
$I_{RRM}$	Maximum Reverse Leakage Current	V <sub>R</sub> =1200V	$T_j = 25^{\circ}C$			250	μΑ
$I_{\mathrm{F}}$	DC Forward Current		$T_{j} = 150^{\circ}C$ $T_{C} = 80^{\circ}C$		400	2000	A
14	De l'orward current		-				Λ
$V_{\mathrm{F}}$	Diode Forward Voltage	$I_F = 400A$ $V_{GE} = 0V$	$T_j = 25^{\circ}C$		1.7	2.2	V
V F			$T_{j} = 150^{\circ}C$		1.65		
4	Reverse Recovery Time	$I_F = 400A$ $V_R = 600V$ $di/dt = 7000A/\mu s$	$T_j = 25$ °C		155		ns
t <sub>rr</sub>			$T_{j} = 150^{\circ}C$		300		
	n n cl		$T_i = 25^{\circ}C$		37.2		μС
$Q_{rr}$	Reverse Recovery Charge		$T_{\rm j} = 150^{\circ}{\rm C}$		78		
Е	Reverse Recovery Energy	·	$T_j = 25^{\circ}C$		16		mJ
E <sub>rr</sub>			$T_{\rm j} = 150^{\circ}{\rm C}$		32		1113



### Thermal and package characteristics

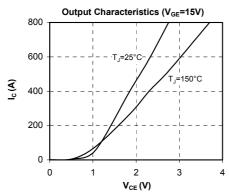
Symbol	Characteristic			Min	Typ	Max	Unit	
$R_{thJC}$	Junction to Case Thermal Resistance  IGBT  Diode		IGBT			0.072	°C/W	
1\(\text{thJC}\)			Diode			0.14	C/ VV	
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V	
$T_{J}$	Operating junction temperature range			-40		175		
$T_{STG}$	Storage Temperature Range			-40		125	°C	
$T_{\rm C}$	Operating Case Temperature			-40		125		
Torque	Mounting forque	For terminals	M6	3		5	N.m	
		To Heatsink	M6	3		5	18.111	
Wt	Package Weight					350	g	

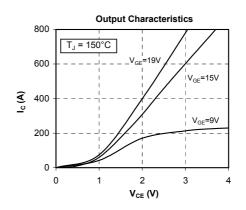
### D3 Package outline (dimensions in mm)

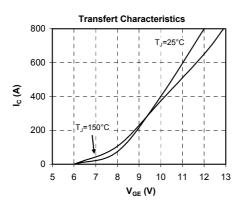


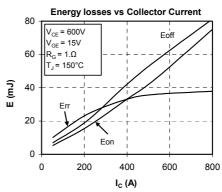


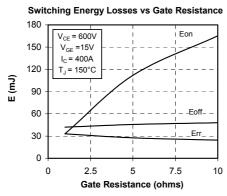
### **Typical Performance Curve**

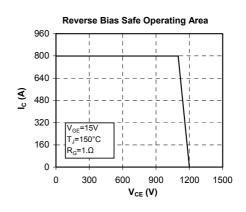


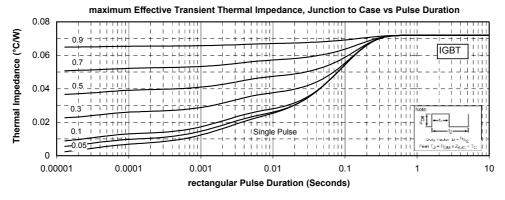




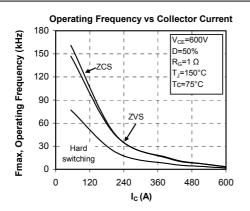


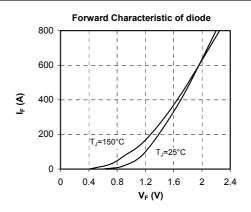


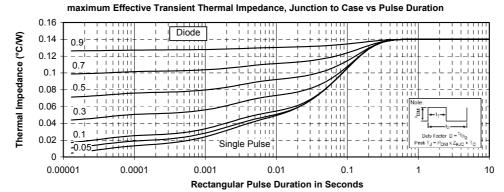












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